

# Kyung-Hwan Jin

## List of Publications by Year in descending order

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44

papers

1,481

citations

318942

23

h-index

355658

38

g-index

44

all docs

44

docs citations

44

times ranked

2576

citing authors

#	ARTICLE	IF	CITATIONS
1	Prediction of intrinsic topological superconductivity in Mn-doped GeTe monolayer from first-principles. <i>Npj Computational Materials</i> , 2021, 7, .	3.5	15
2	Distinguishing a Mott Insulator from a Trivial Insulator with Atomic Adsorbates. <i>Physical Review Letters</i> , 2021, 126, 196405.	2.9	37
3	Enhanced Berry Curvature Dipole and Persistent Spin Texture in the Bi(110) Monolayer. <i>Nano Letters</i> , 2021, 21, 9468-9475.	4.5	22
4	Honeycomb-Lattice Mott Insulator on Tantalum Disulphide. <i>Physical Review Letters</i> , 2020, 125, 096403.	2.9	8
5	1D topological phases in transition-metal monochalcogenide nanowires. <i>Nanoscale</i> , 2020, 12, 14661-14667.	2.8	15
6	Doping-induced topological phase transition in Bi: The role of quantum electronic stress. <i>Physical Review B</i> , 2020, 101, .	1.1	11
7	Theory of Epitaxial Growth of Borophene on Layered Electride: Thermodynamic Stability and Kinetic Pathway. <i>Journal of Physical Chemistry C</i> , 2020, 124, 6063-6069.	1.5	7
8	Prediction of room-temperature multiferroicity in strained MoCr <sub>2</sub> S <sub>6</sub> monolayer. <i>Journal of Applied Physics</i> , 2020, 127, 155302.	1.1	4
9	Weyl points created by a three-dimensional flat band. <i>Physical Review B</i> , 2019, 99, .	1.1	23
10	Topological superconducting phase in high-T <sub>c</sub> superconductor MgB <sub>2</sub> with Diracâ€“nodal-line fermions. <i>Npj Computational Materials</i> , 2019, 5, .	3.5	52
11	A 2D nonsymmorphic Dirac semimetal in a chemically modified group-VA monolayer with a black phosphorene structure. <i>Nanoscale</i> , 2019, 11, 7256-7262.	2.8	22
12	Observation of topological surface states in the high-temperature superconductor $MgTa_2$ . <i>Physical Review B</i> , 2019, 100, .	2.8	22
13	Topological Electride Y <sub>2</sub> C. <i>Nano Letters</i> , 2018, 18, 1972-1977.	4.5	67
14	Formation of a large gap quantum spin Hall phase in a 2D trigonal lattice with three p-orbitals. <i>Nanoscale</i> , 2018, 10, 5496-5502.	2.8	13
15	Alloy Engineering of Topological Semimetal Phase Transition in $MgTa_2$ . <i>Physical Review Letters</i> , 2018, 120, 136103.	2.8	22
16	Nanoperforated graphene with alternating gap switching for optical applications. <i>Carbon</i> , 2018, 126, 480-488.	5.4	15
17	Pseudo Dirac nodal sphere semimetal. <i>Physical Review B</i> , 2018, 98, .	1.1	29
18	Black-hole horizon in the Dirac semimetal Zn <sub>2</sub> In <sub>2</sub> S <sub>5</sub> . <i>Physical Review B</i> , 2018, 98, .	1.1	67

#	ARTICLE	IF	CITATIONS
19	Intrinsic quantum anomalous hall effect in a two-dimensional anilato-based lattice. <i>Nanoscale</i> , 2018, 10, 11901-11906.	2.8	29
20	Tunable topological semimetal states with ultraflat nodal rings in strained YN. <i>Physical Review B</i> , 2018, 98, .	1.1	21
21	Bending strain engineering in quantum spin hall system for controlling spin currents. <i>Nature Communications</i> , 2017, 8, 15850.	5.8	23
22	Quantum Spin Hall Effect and Tunable Spin Transport in As-Graphane. <i>Nano Letters</i> , 2017, 17, 4359-4364.	4.5	15
23	Computational design of two-dimensional topological materials. <i>Wiley Interdisciplinary Reviews: Computational Molecular Science</i> , 2017, 7, e1304.	6.2	38
24	Nanostructured topological state in bismuth nanotube arrays: inverting bonding-antibonding levels of molecular orbitals. <i>Nanoscale</i> , 2017, 9, 16638-16644.	2.8	6
25	Atomically Abrupt Topological p-n Junction. <i>ACS Nano</i> , 2017, 11, 9671-9677.	7.3	26
26	Creation of half-metallic $f$ -orbital Dirac fermion with superlight elements in orbital-designed molecular lattice. <i>Physical Review B</i> , 2017, 96, .	1.1	10
27	$Cmce$ -phase $\text{Ag}_2\text{S}$ interface orbital engineering of large-gap topological states: Decorating gold on a Si(111) surface. <i>Physical Review B</i> , 2017, 96, .	1.1	29
28	Quantum spin Hall phase in 2D trigonal lattice. <i>Nature Communications</i> , 2016, 7, 12746.	5.8	43
29	Topological phase transition and quantum spin Hall edge states of antimony few layers. <i>Scientific Reports</i> , 2016, 6, 33193.	1.6	38
30	Large-Gap Quantum Spin Hall State in MXenes: $d$ -Band Topological Order in a Triangular Lattice. <i>Nano Letters</i> , 2016, 16, 6584-6591.	4.5	193
31	Band structure engineering of topological insulator heterojunctions. <i>Physical Review B</i> , 2016, 93, .	1.1	30
32	Topological fate of edge states of single Bi bilayer on Bi(111). <i>Physical Review B</i> , 2016, 93, .	1.1	26
33	Interface orbital engineering of large-gap topological states: Decorating gold on a Si(111) surface. <i>Physical Review B</i> , 2016, 93, .	1.1	32
34	Spin rectification by orbital polarization in Bi-bilayer nanoribbons. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 8637-8642.	1.3	13
35	Electronic structure evolution of single bilayer Bi(111) film on 3D topological insulator Bi <sub>2</sub> Se <sub>3</sub> surfaces. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 255501.	0.7	14
36	Quantum Oscillation Signatures of Pressure-induced Topological Phase Transition in BiTeI. <i>Scientific Reports</i> , 2015, 5, 15973.	1.6	25

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37	Proximity Effect Induced Electronic Properties of Graphene on Bi <sub>2</sub> Te <sub>2</sub> Se. ACS Nano, 2015, 9, 10861-10866.		7.3	36
38	Quantum anomalous Hall and quantum spin-Hall phases in flattened Bi and Sb bilayers. Scientific Reports, 2015, 5, 8426.		1.6	66
39	Transforming a surface state of a topological insulator by a Bi capping layer. Physical Review B, 2014, 90, .		1.1	9
40	Edge and interfacial states in a two-dimensional topological insulator: Bi(111) bilayer on $\text{Bi}_{2}\text{Te}_{3}$ . Physical Review B, 2014, 89, .			
41	Proximity-induced giant spin-orbit interaction in epitaxial graphene on a topological insulator. Physical Review B, 2013, 87, .		1.1	94
42	Effect of atomic impurities on the helical surface states of the topological insulator Bi <sub>2</sub> Te <sub>3</sub> . Journal of Physics Condensed Matter, 2012, 24, 175001.		0.7	17
43	Controlling the self-doping of epitaxial graphene on SiC via Ar ion treatment. Physical Review B, 2011, 84, .		1.1	23
44	Crossover in the adsorption properties of alkali metals on graphene. Physical Review B, 2010, 82, .		1.1	86